



Product Overview

NSS1C200: Low $V_{CE(sat)}$ Transistor, PNP, 100 V, 2.0 A

For complete documentation, see the data sheet

Product Description

Low $V_{CE(sat)}$ Bipolar Junction Transistors (BJT) are miniature surface mount devices featuring ultra low saturation voltage $V_{CE(sat)}$ and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Features

- High Current, Low $V_{CE(sat)}$, ESD Robust, High Current Gain, High Cut Off Frequency, Low Profile Package, Linear Gain (Beta)
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AECQ101 Qualified and PPAP Capable

Benefits

- Improved Circuit Efficiency, Decreased Battery Charge Time, Reduce component count, High Frequency Switching, Smaller Portable Product, No distortion

Applications

- Load Switching, Battery Charging, External Pass Transistor, DC/DC Converter, Complimentary Driver, Current Extension & Low Drop Out Regulation, Cathode Florescent Lamp drive, Peripheral Driver - LEDs, Motors, Relays

End Products

- Mobile Phones, PDAs, MP3 players, Computers, Power Supplies, Automotive Body Electronics, Toys.

Part Electrical Specifications

Product	Compliance	Status	Polarity	I_C Continuous (A)	$V_{(BR)CEO}$ Min (V)	$V_{CE(sat)}$ Max (V)	h_{FE} Min	h_{FE} Max	f_T Min (MHz)	P_{TM} Max (W)	Package Type
NSS1C200MZ4T1G	AEC Qualified Pb-free Halide free	Active	PNP	2	100	0.125	120	360	100	2	SOT-223-4 / TO-261-4
NSS1C200MZ4T3G	AEC Qualified Pb-free Halide free	Active	PNP	2	100	0.125	120	360	100	2	SOT-223-4 / TO-261-4
NSV1C200MZ4T1G	AEC Qualified PPAP Capable Pb-free Halide free	Active	PNP	2	100	0.125	120	360	100	2	SOT-223-4 / TO-261-4

For more information please contact your local sales support at www.onsemi.com

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